MOSPEC

SILICON NPN POWER TRANSISITORS

... designed for medium-speed switching and amplifier applications

FEATURES

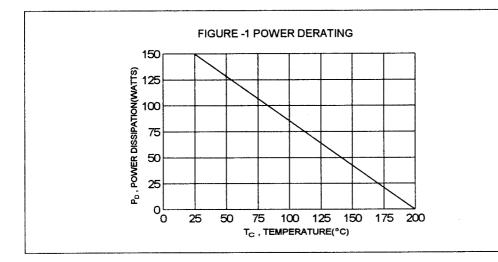
- * Gain Ranged Specified at 1A and 3A.
- * Low V_{CE(sat)}: typically 0.5 V @ I_C=5 A , I_B=0.5A * Excellent Safe Operating Areas
- * Complementary PNP Types Available 2N3789 thru 2N3792

MAXIMUM RATINGS

Characteristic	Symbol	2N3713 2N3715	2N3714 2N3716	Unit
Collector-Base Voltage	V _{CBO}	80 100		v
Collector-Emitter Voltage	V _{CEO}	60 80		v
Emitter-Base Voltage	V _{EBO}		v	
Collector Current - Continuous	l _c	10		A
Base Current-Continuous	l _B	4		A
Total Power Dissipation @T _c =25°C Derate above 25°C	PD	150 0.857		W W/°C
Operating and Storage Junction Temperature Range	T _J ,T _{STG}	-65 to	°C	

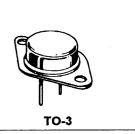
THERMAL CHARACTERISTICS

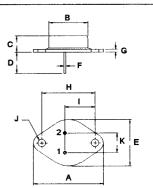
Characteristic	Symbol	Мах	Unit
Thermal Resistance Junction to Case	Rθ jc	1.17	°C/W



NPN 2N3713 Thru 2N3716

10 AMPERE POWER TRANSISTORS NPN SILICON 60-80 VOLTS 150 WATTS





PIN 1.BASE 2.EMITTER COLLECTOR(CASE)

	MILLIMETERS			
DIM	MIN	MAX		
Α	38.75	39.96		
В	19.28	22.23		
С	7.96	9.28		
D	11.18	12.19		
Е	25.20	26.67		
F	0.92	1.09		
G	1.38	1.62		
н	29.90	30.40		
. 1	16.64	17.30		
J	3.88	4.36		
к	10.67	11.18		

2N3713 Thru 2N3716 NPN

ELECTRICAL CHARACTERISTICS ($T_c = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage (1) (I _C = 200 mA, I _B = 0)	2N3713, 2N3715 2N3714, 2N3716	V _{CEO (sus)}	60 80		v
Collector -Emitter Cutoff Current $(V_{cE} = 80 V, V_{BE(off)} = -1.5V)$ $(V_{cE} = 100 V, V_{BE(off)} = -1.5V)$ $(V_{cE} = 60 V, V_{BE(off)} = -1.5V, T_c = 150^{\circ}C)$ $(V_{cE} = 80 V, V_{BE(off)} = -1.5V, T_c = 150^{\circ}C)$	2N3713, 2N3715 2N3714, 2N3716 2N3713, 2N3715 2N3714, 2N3716	I _{CEX}		1.0 1.0 10 10	mA
Emitter Cutoff Current (V _{EB} = 7.0 V, I _C =0)	All Types	I _{EBO}		5.0	mA

ON CHARACTERISTICS (1)

DC Current Gain		hFE			
(I _c = 1.0 A, V _{cE} = 2.0 V)	2N3713, 2N3714		25	90	
	2N3715, 2N3716		50	180	
(I _c = 3.0 A, V _{ce} = 2.0 V)	2N3713, 2N3714		15		
	2N3715, 2N3716		30		
Collector-Emitter Saturation Voltage		V _{CE(sat)}			v
(I _C = 5.0 A, I _B = 0.5 A)	2N3713, 2N3714	CE(sat)		1.0	
	2N3715, 2N3716			0.8	
Base-Emitter Saturation Voltage		V _{BE(sat)}			v
(I _c = 5.0 A, I _B = 0.5 A)	2N3713, 2N3714	DE(sat)		2.0	
	2N3715, 2N3716			1.5	
Base-Emitter On Voltage		V _{BE(on)}			V
(I _c = 3.0 A, V _{cE} = 2.0 V)	All Types	22(01)		1.5	

DYNAMIC CHARACTERISTICS

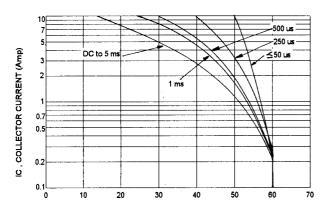
Current-Gain Bandwidth Product	f _T		MHz
(I _c = 500 mA,V _{ce} = 10 V, f = 1MHz)	•	4.0	

(1) Pulse Test: Pulse width = 300 us , Duty Cycle $\leq 2.0\%$ (2) f_{T} = $~\left|h_{f_{0}}\right|$ ° f $_{test}$

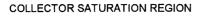
2N3713 thru 2N3716 NPN

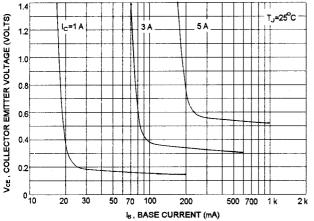
2N3713,2N3715

ACTIVE REGION SAFE OPERATING AREA

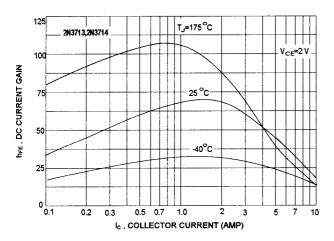


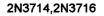
VCE , COLLECTOR EMITTER VOLTAGE (VOLTS)



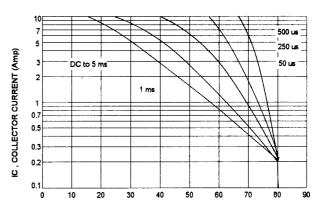






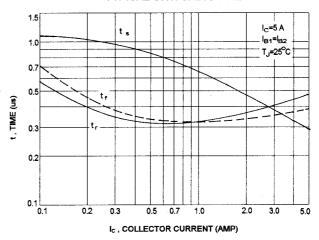


ACTIVE REGION SAFE OPERATING AREA

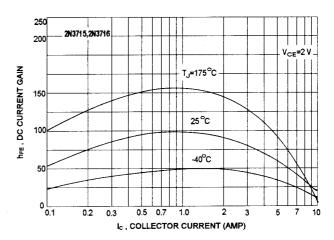


VCE , COLLECTOR EMITTER VOLTAGE (VOLTS)





DC CURRENT GAIN



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